

# SMPD... Power meets SMD

(Surface Mount Power Device)



February 2013

## Overview:

The demand for higher power density in system design is continually driving innovation in semiconductor packaging technology. IXYS continues to be at the forefront of this development with its new isolated package family SMPD™ (Surface Mount Power Device). The IXYS design cornerstone of "MORE POWER − LESS PACKAGE" has resulted in the SMPD™ module range which efficiently provides solutions for applications where traditional offerings create problems such as larger module footprints, higher cost and longer cycle times in assembly and the problem that catalogue items rarely provide the best silicon content.

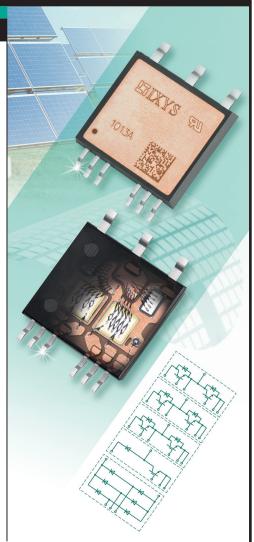
IXYS' ISOPLUS™ isolation technology has for many years provided a UL recognized rugged isolation platform for a wide range of leading power modules. The SMPD™ range now extends its ISOPLUS™ portfolio to include modules that can be assembled in standard surface mount (SMD) soldering processes and is pick-and-place ready to be assembled on customer's existing SMD assembly lines. The ISOPLUS™ advantage also includes:

- Isolated package using IXYS' own Direct Copper Bonded (DCB) substrates
- · Voltage isolation up to 2500V (UL Recognized)
- Lower junction-to-heat sink thermal resistance
- Improved temperature and power cycling performance
- Higher reliability than copper based modules
- Very small coupling capacitance -> Reduced EMI
- Reduced parasitic inductance -> Optimized Switching Performance
- Replacement of multiple discrete reduces system size
- Shorter time to market in providing optimized silicon die content

The IXYS SMPD™ range provides not only a large array of standard options in terms of topology or silicon varieties. Its simplicity by design and optimized manufacturing process can allow fast time to market for customers that require differing die and circuit combinations effectively fast tracking product development. IXYS removes the need for more expensive competitive solutions and can successfully combine numerous discrete devices in one high reliability package that can then be easily assembled on current SMD assembly lines.

Added to this the IXYS SMPD<sup>TM</sup> provides the ideal modular circuit building blocks so that the designer can select the ideal solution. For instance one SMPD can provide a solution for each stage of a Motor Inverter – 1x SMPD<sup>TM</sup> for the three phase diode input rectifier, 1xSMPD<sup>TM</sup> for the Brake or PFC stage and 3xSMPD<sup>TM</sup> for the 3 phase IGBT inverter. The customer can then select where to position each stage to optimize his heat sink or cooling solution often downsizing materials.

The IXYS SMPD™ range provides a solution-scale package reducing material waste and lowering power footprint for all the power electronic applications of today and those of the future. Its platform flexibility and ease in assembly provides cost efficiency not just in terms of module cost but in the important processes of system design, time to market and product assembly.





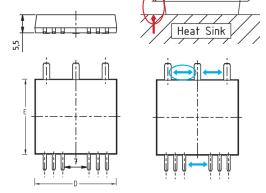




#### **SUMMARY TABLE – SMPD**

Part Number	Pack.	V <sub>CES</sub>	I <sub>C25</sub>	Config.	Part Number	Pack.	V <sub>CES</sub>	I <sub>C25</sub> (A)	Config.	Part Number	Pack.	V <sub>CES</sub>	I <sub>C25</sub> (A)	Config.
DIODE														
DPG60B600LB	В	600	62	•	DHG60U1200LB	В	1200	62	°	DSA120X150LB	В	150	75	- <b>f</b> - <b>f</b> !
DHG50B1200LB	В	1200	50	**	DMA90U1800LB	В	1800	99		DSA120X200LB	В	200	75	<del>                                      </del>
DLA100B1200LB	В	1200	124	**						DSA240X200LB	В	200	120	
IGBT														
MMIX1X200N60B3	Χ	600	175	्रं	MMIX2S50N60B4D1	Χ	600	50	•	MPC40RK600LB	В	600	52	•
MMIX1G320N60B3	Χ	600	400	~(L)	IXA20PG1200DHGLB	В	1200	32	┙╬╅	IXA20RG1200DHGLB	В	1200	32	*
MMIX1G75N250	Χ	2500	110		IXA30PG1200DHGLB	В	1200	43	•	IXA30RG1200DHGLB	В	1200	43	•
					IXA40PG1200DHGLB	В	1200	61	┙Қ★	IXA40RG1200DHGLB	В	1200	61	مالم
MMIX1X100N60B3H1	Χ	600	105	٩	IXA40PF1200TDHGLE	3 B	1200	61	$\longrightarrow$					
MMIX1X200N60B3H1	Χ	600	175							IXA20PT1200LB	В	1200	32	
MMIX1Y82N120C3H1	Χ	1200	78	~ <del>\\\</del>										
MMIX1Y100N120C3H	1 X	1200	92	٥										<b>~</b>   <b>√</b>   <b></b>
MOSFET										HV-IGBT/BIMOSFET				
MMIX1T600N04T2	Χ	40	600	٩	MKE38P600LB	В	600	50	•—1	MMIX4G20N250 <sup>1</sup>	Χ	2500	23	
MMIX1T550N055T2	Χ	55	550	(H)						MMIX4B12N300	Χ	3000	26	
MMIX1F520N075T2	Χ	75	500						•	MMIX4B20N300	Χ	3000	34	
MMIX1F420N10T	Χ	100	334										•	
MMIX1F360N15T2	Χ	150	235										~  <u> </u>	~L
MMIX1F230N20T	Χ	200	168										•	<u>-</u>
MMIX1F180N25T	Χ	250	130		MKE38RK600DFELB	В	600	50	•					, <del>                                     </del>
MMIX1F160N30T	Χ	300	102										┙┞┑╇	~-  <b>\</b> _{1}*
MMIX1F210N30P3	Χ	300	108											
MMIX1F132N50P3	Χ	500	63					•	ا لــ					
MMIX1F44N100Q3	Χ	1000	24											
MMIX1F40N110P	Χ	1100	30							<sup>1</sup> without diode				

#### PACKAGE B



#### **SMPD**

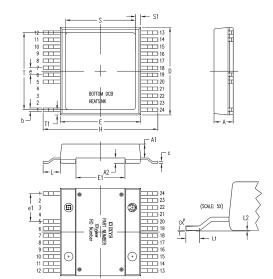
→ improved creepage and clearance distance

Pin – Heat Sink: 4,0 mm min

Pin – Pin: 7,0 mm min



### PACKAGE X



CVM	INC	CHES	MILLIMETERS				
SYM	MIN	MAX	MIN	MAX			
Α	.209	.224	5.30	5.70			
A1	.154	.161	3.90	4.10			
A2	.055	.063	1.40	1.60			
b	.035	.045	0.90	1.15			
С	.018	.026	0.45	0.65			
D	.976	.994	24.80	25,25			
Ε	.898	.915	22.80	23,25			
E1	.543	.559	13.80	14.20			
е	.07	9 BSC	2.00 BSC				
e1	.31	5 BSC	8.00 B2C				
Н	1.272	1.311	32.30	33.30			
L	.181	.209	4.60	5.30			
L1	.051	.067	1.30	1.70			
L2	.000	.006	0.00	0.15			
S	.742	.792	18.85	20.12			
S1	.057	.082	1.45	2.08			
Τ	.823	.873	20.90	22.17			
T1	.056	.080	1.42	2.03			
X	0	4°	0	4°			

NOTE:
1. Bottom heatsink meets 2.6KV AC isolation to the other pins.
2. All leads are matte pure tin plated.